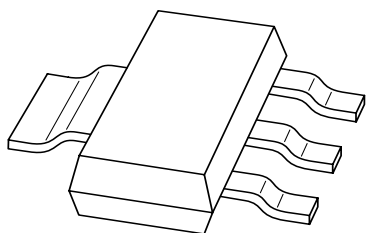


DATA SHEET



BCP51; BCP52; BCP53 PNP medium power transistors

Product specification
Supersedes data of 2001 Oct 10

2003 Feb 06

PNP medium power transistors

BCP51; BCP52; BCP53

FEATURES

- High collector current
- 1.3 W power dissipation.

APPLICATIONS

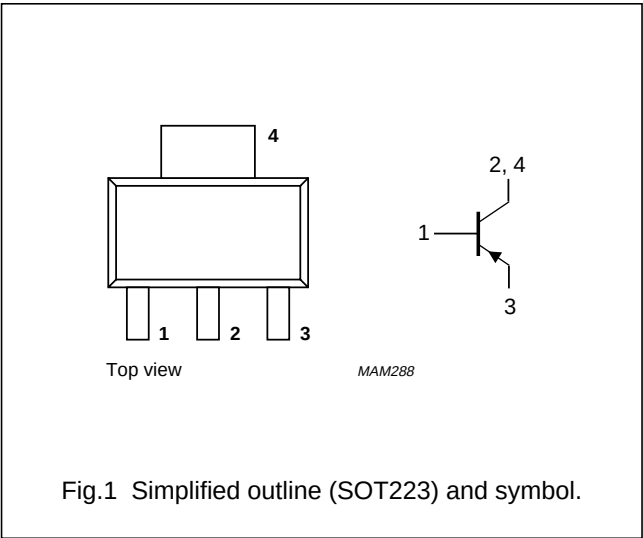
- General purpose medium power DC applications
- Low and medium frequency AC applications
- Peripheral drivers
- Linear voltage regulators and battery chargers.

DESCRIPTION

PNP medium power transistor in a SOT223 plastic package. NPN complements: BCP54, BCP55 and BCP56.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-80	V
I_C	collector current (DC)	-1	A
I_{CM}	peak collector current	-1.5	A

PNP medium power transistors

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCP51		–	–45	V
	BCP52		–	–60	V
	BCP53		–	–100	V
V _{CEO}	collector-emitter voltage	open base			
	BCP51		–	–45	V
	BCP52		–	–60	V
	BCP53		–	–80	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–1	A
I _{CM}	peak collector current		–	–1.5	A
I _{BM}	peak base current		–	–0.2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.3	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	95	K/W
R _{th j-s}	thermal resistance from junction to soldering point		14	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

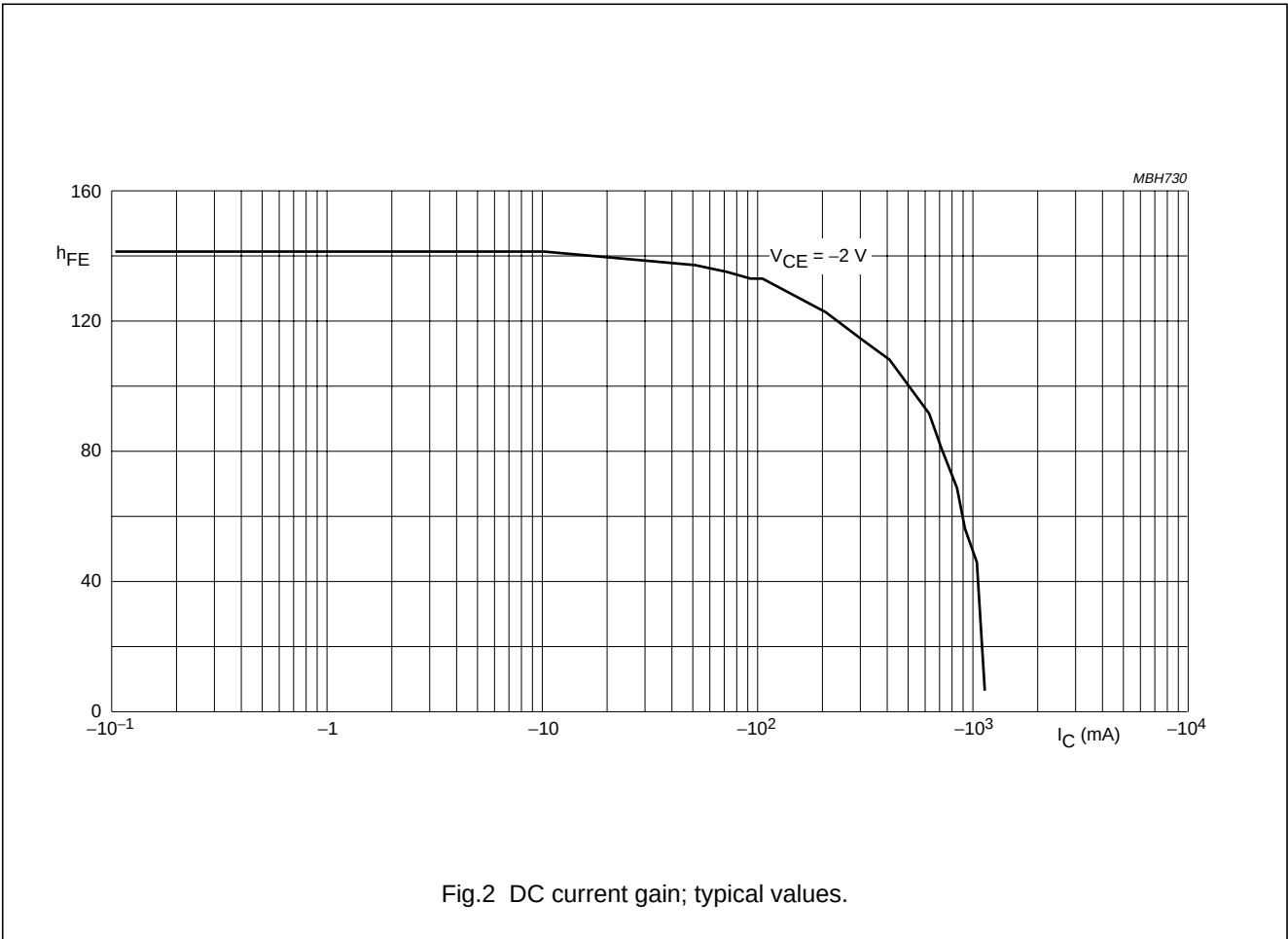
PNP medium power transistors

BCP51; BCP52; BCP53

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	-	-	-100	nA
		I _E = 0; V _{CB} = -30 V; T _j = 125 °C	-	-	-10	µA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = -5 V	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; see Fig.2				
		I _C = -5 mA	63	-	-	
		I _C = -150 mA	63	-	250	
		I _C = -500 mA	40	-	-	
h _{FE}	DC current gain	I _C = -150 mA; V _{CE} = -2 V; see Fig.2				
	BCP51-10; BCP52-10; BCP53-10		63	-	160	
	BCP51-16; BCP52-16; BCP53-16		100	-	250	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA	-	-	-0.5	V
V _{BE}	base-emitter voltage	I _C = -500 mA; V _{CE} = -2 V	-	-	-1	V
f _T	transition frequency	I _C = -10 mA; V _{CE} = -5 V; f = 100 MHz	-	115	-	MHz



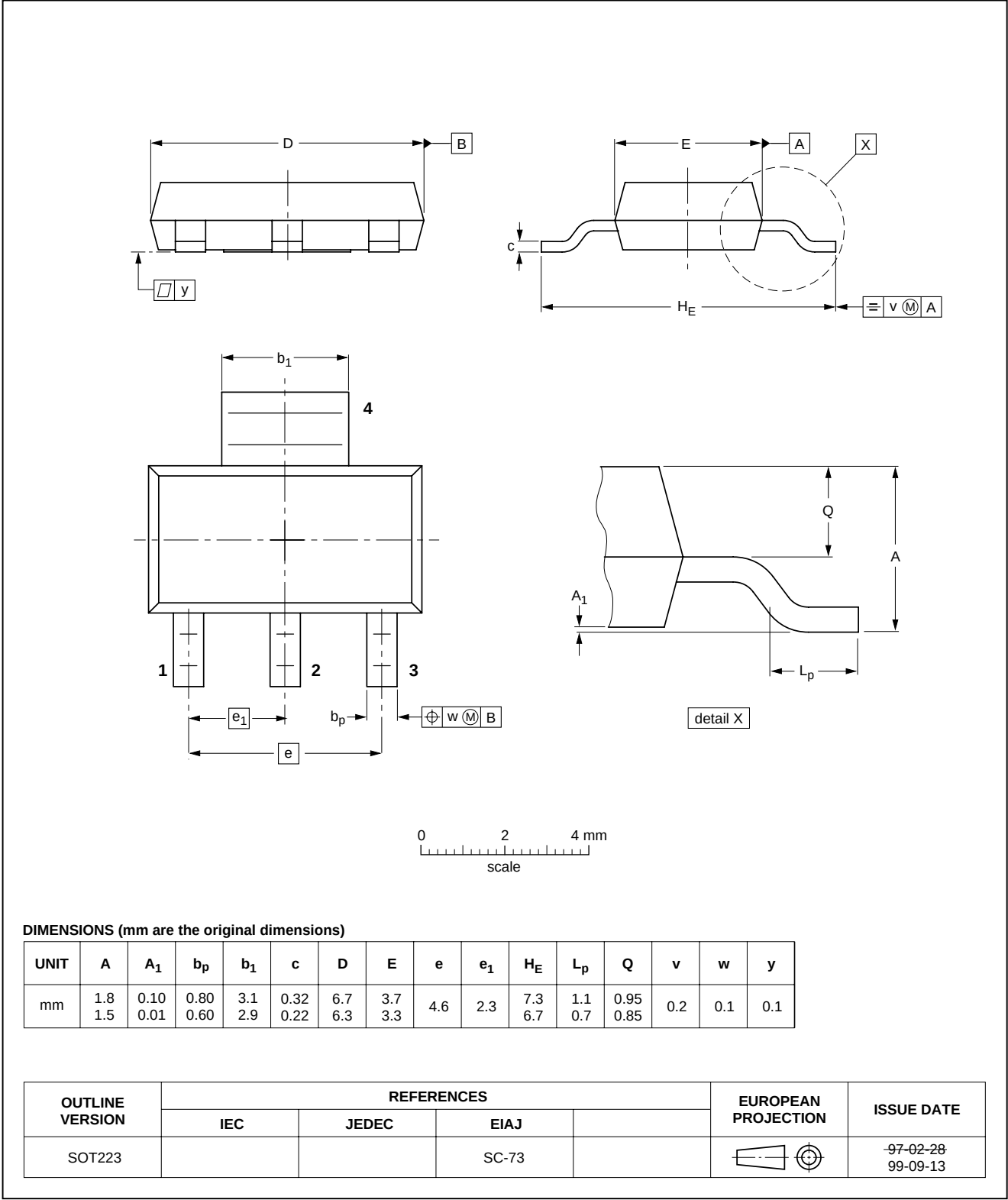
PNP medium power transistors

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



PNP medium power transistors

BCP51; BCP52; BCP53

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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NOTES

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